

VM7160

2, 4 OR 8-CHANNEL, 5-VOLT, THIN-FILM HEAD, READ/WRITE PREAMPLIFIER WITH MULTIPLE SERVO WRITE CAPABILITY

PRELIMINARY

July, 1993

FEATURES

- · High Performance
 - Read Gain = 200 300 V/V Typical
 - Input Noise = 0.65nV/√Hz max
 - Head Inductance Range = 0.2 5 µH (0.5 µH typical)
 - Write Current Range 5 35 mA
 - Low Input Capacitance = 12 pF typical
- TTL Write Data Inputs
- · Servo Write Two or Four Channels at the Same Time
- VM7162 Two-Channel Servo Write
- VM7164 Four-Channel Servo Write
- VM7168 Two Banks of Four-Channel Servo Write
- Very Low Power Dissipation = 4.5 mW Typical in Sleep Mode
- · Power Up/Down Data Protect Circuitry
- Fast Write-to-Read and Read-to-Write Recovery Time
- Single Power Supply = 5 V ± 10%
- Fault Detect Capability
- Designed for 2-Terminal Thin-Film or MIG Heads
- Other Read Gain Options Available
- Available in 2, 4 or 8-Channels

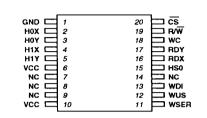
DESCRIPTION

The VM7160 is a high-performance, very low-power read/ write preamplifier designed for use with external 2-terminal, thin-film or MIG recording heads. This circuit will operate on a single 5-volt power supply and is ideally suited for use in battery powered disk drives. The VM7160 provides a two or four channel servo write feature, enabling the user to write servo information directly through the preamp.

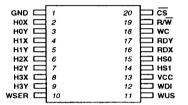
The VM7160 provides write current switching in the write mode and a low noise data path in the read mode for up to eight read/write recording heads. When deactivated, the device enters a *sleep mode* that reduces power dissipation to 4.5 mW. Data protection circuitry is provided to ensure that the write current source is totally disabled during power supply power up/power down conditions. Write-to-read recovery time is minimized by eliminating common mode output voltage swings when switching between modes.

The VM7160 is available in several different packages. Please consult VTC for package availability and additional read mode voltage gains.

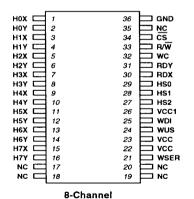
CONNECTION DIAGRAMS



2-Channel 20-lead SSOP

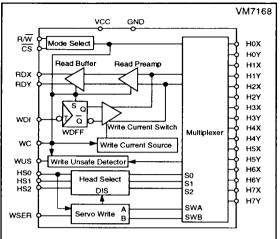


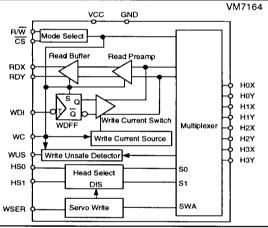
4-Channel 20-lead SOIC, SSOP

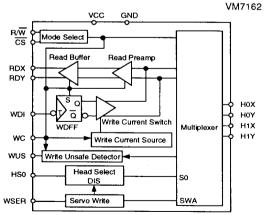


36-lead SOIC

BLOCK DIAGRAMS







ABSOLUTE MAXIMUM RATINGS

Power Supply:
V _{CC} 0.3V to +7V
Write Current I _W 60mA
Input Voltages:
Digital Input Voltage V _{IN} 0.3V to (V _{CC} + 0.3)V
Head Port Voltage V _H 0.3V to (V _{CC} + 0.3)V
WUS Pin Voltage Range V _{WUS} 0.3V to +6V
Output Current:
RDX, RDY: I _O 10mA
WUS: I _{WUS} +12mA
Junction Temperature
Storage Temperature T _{stq} 65° to 150°C
Thermal Characteristics, Θ_{JA} :
16-lead SOIC 100°C/W
20-lead SOIC 80°C/W
20-lead SSOPTBD
36-lead SOIC

RECOMMENDED OPERATING CONDITIONS

Power Supply Voltage:	
V _{CC}	+5V ± 10%
Write current (I _W)	1 to 40mA
Head Inductance (LH)	0.2 to 10μH
Junction Temperature (T _J)	. 25°C to 125°C

CIRCUIT OPERATION

The VM7162 addresses two two-terminal thin-film heads, providing write drive or read amplification. Head selection and mode control are accomplished with pins WSER, HS0, CS and R/W, as shown in Tables 1a and 2a.

The VM7164 addresses four two-terminal thin-film heads, providing write drive or read amplification. Head selection and mode control are accomplished with pins WSER, HS0, HS1, $\overline{\text{CS}}$ and $\overline{\text{R/W}}$, as shown in Tables 1b and 2b.

The VM7168 addresses eight two-terminal thin-film heads, providing write drive or read amplification. Head selection and mode control are accomplished with pins HS0, HS1, HS2, WSER, CS and R/W, as shown in Tables 1c and 2c.

On all versions, internal pull-up resistors on pins \overline{CS} and $\overline{R/W}$ will force the device into a non-writing condition if either control line is opened accidentally.

Write Mode

In write mode, the VM7160 acts as a write current switch with the write unsafe (WUS) detection circuitry activated. Write current is toggled between the X and Y side of the selected head on each high to low transition on the Write Data Flip-Flop (WDFF) so that upon switching to the write mode, the write current flows into the "X" side of the head.

The write current magnitude is determined by an external resistor (R_{WC}) connected between the WC pin and Ground. An internally generated reference voltage is present at the WC pin. The magnitude of the Write Current (0-PK, \pm 8%) is:

$$I_W = K_W/R_{WC} + 0.2mA$$

= 50/R_{WC} + 0.2mA

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Power supply fault protection ensures data security on the disk by disabling the write current source during a power supply voltage fault or by supply power up/down conditions. Additionally, the write unsafe (WUS) detection circuitry will flag any of the conditions listed below, as a high level on the WUS line. Two negative transitions on the WDI pin, after the fault is corrected, is required to clear the WUS line.

- No write current
- WDI frequency too low
- Read or sleep mode

Servo Write Mode

In servo write mode, two channels of the VM7162 are active at the same time. Pin WSER controls the servo mode. When WSER and R/W are low, the chip is in normal write mode: one head is written at a time based on the state of the head select line. When WSER is high and R/W is low, the chip is in servo write mode, where the heads are written independent of the head select line (see table 1a).

In servo write mode, four channels of the VM7164 are active at the same time. Pin WSER controls the servo mode. When WSER and R/W are low, the chip is in normal write mode: one head is written at a time based on the state of the head select lines. When WSER is high and R/W is low, the chip is in servo write mode: four channels are written at the same time, independent of the head select lines (see table 1b).

In servo write mode, four channels of the VM7168 are active at the same time. Pin WSER controls the servo mode and HS0 controls which four heads are simultaneously written. When WSER is high and R/W is low, the chip is in servo write mode: four channels are written at the same time dependent on the state of HS0. When HS0 = 0, heads 0, 2, 4 and 6 are written, and when HS0 = 5V, heads 1, 3, 5 and 7 are written (see table 1c). When WSER is low, the chip is in normal write mode: one head is written at a time based on the state of the head select lines.

On all versions, an internal pull-down resistor on pin WSER will force the device into single head write mode if the control line is accidentally opened.

Read Mode

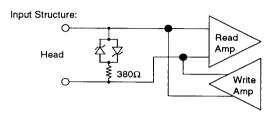
In read mode, the VM7160 acts as a low noise differential amplifier for signals coming off the disk. The write current generator and write unsafe circuitry is deactivated. The RDX, RDY pins are emitter follower outputs and are in phase with "X" and "Y" head ports. These outputs should be AC coupled to the load. The RDX, RDY common mode output voltage is constant, minimizing the transient between read and write mode, thereby, substantially reducing the recovery time in the Pulse Detector circuit connected to these outputs.

Sleep Mode

When \overline{CS} is high, initially all circuitry is shut down so that power dissipation is reduced to 4.5 mW in the *Sleep Mode*. Switching the \overline{CS} line low *wakes up* the chip and the device will enter the read or write mode, depending on the status of the \overline{RW} line.

Diode Connected Damping Resistor (patent pending)

The VM7162 has an optional damping resistors isolated by Schottky diodes. The diodes effectively remove the resistor from the circuit during the read mode, however during the write mode with the higher level input signal, the resistor provides damping for the write current waveform.



Please consult factory for damping resistor options on other devices.

Table 1a: Mode Selection for VM7162

R/W	<u>cs</u>	WSER	Mode
0	0	0	Write Single
1	0	Х	Read
Х	1	Х	Idle
0	0	1	Write Servo (head 0,1)

Table 1b: Mode Selection for VM7164

R∕W	<u>cs</u>	WSER	Mode
0	0	0	Write Single
1	0	х	Read
Х	1	х	Idle
0	0	1	Write Servo (head 0,1,2,3)

Table 1c: Mode Selection for VM7168

	R∕W	cs	WSER	HS0	Mode
	0	0	0	Х	Write Single
Г	1	0	Х	Х	Read
	Х	1	×	Х	Idle
	0	0	1	0	Write Servo (head 0,2,4,6)
	0	0	1	1	Write Servo (head 1,3,5,7)

Table 2a: Head Selection in Single Write Mode (WSER = LOW) for VM716N2

HS0	Head
0	0
1	1

Table 2b: Head Selection in Single Write Mode (WSER = LOW) for VM716N4

HS1	HS0	Head
0	0	0
0	1	1
1	0	2
1	1	3

Table 2c: Head Selection in Single Write Mode (WSER = LOW) for VM716N8

HS2	HS1	HS0	Head
0	0	0	0
0	0	1	1
0	1	0	2
0	1	1	3
1	. 0	0	4
1	0	1	5
1	1	0	6
1	1	1	7

PIN DESCRIPTIONS

PIN DESCRIPTIONS						
NAME	1/0	DESCRIPTION				
HS0-HS2	*	Head Select: selects one of up to 8 heads				
H0X-H7X H0Y-H7Y	1/0	X, Y Head terminals				
WDI	*	Write Data Inputs: TTL input signal, negative transition toggles direction of head current.				
cs	ı	Chip select: high level signal puts chip in sleep mode, low level wakes chip up				
R/W	1*	Read/Write select: High level selects read mode, low-level selects write mode				
wus	O*	Write unsafe: Open collector output: high level indicates writes unsafe condition				
wc		Write current adjust: A resistor adjusts level of write current				
RDX-RDY	0.	Read data output: differential output data				
vcc		+5 volt supply**				
GND		Ground				
WSER	1*	Servo Write: A high level enables servo mode.				

^{*} May be wire-OR'ed for multi-chip usage.

WRITE CHARACTERISTICS Recommended operating conditions apply unless otherwise specified; $L_H = 1 \mu H$, $R_H = 30 \Omega$, $I_W = 20 mA$, $f_{DATA} = 5 MHz$.

PARAMETER	SYM	CONDITIONS	MIN	TYP (Note 1)	MAX	UNITS
WC Pin Voltage	٧wc			2.5		٧
IWC to Head Current Gain	Aı			20		mA/mA
Write Current Constant	KW	$K_W = (V_{WC})(A_1)$	46	50	54	٧
Write Current Range	lW	1.44K < RWC< 10.4K	5		35	mA
Write Current Tolerance	ΔlW	I _W = 5 - 35mA	-8		+8	%
Differential Head Voltage Swing	VDH			5.4		Vp-p
WDI Transition Frequency for Safe Condition	f _{DATA}	WUS = low	1			MHz
Differential Output Capacitance	СО				15	pF
Differential Output Resistance	Ro	1900	3200			Ω
Unselected Head Transient Current	luH	I _W = 15mA		0.15	1	mA(pk)
RDX, RDY Common Mode Output Voltage	Vсм			V _{CC} -2.7		٧

Note 1: Typical values are given at $V_{CC} = 5V$ and $T_A = 25^{\circ}C$.

^{**} Although both VCC connections are recommended, only one connection is required as both are connected internally.

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DC CHARACTERISTICS Recommended operating conditions apply unless otherwise specified.

PARAMETER	SYM	CONDITIONS	MIN	TYP (Note 1)	MAX	UNITS	
		Read Mode		44	54		
Supply Current		Write Mode, I _W = 35mA Normal VM7162		44 + IW	52 + IW		
	lcc	Normal VM7164 & VM7168		54 + IW	64 + IW	mA	
		Servo VM7162		44 + 2 lW	56 + 2 lW		
		Servo VM7164 & VM7168		70 + 4 lW	82 + 4 lW		
		Sleep Mode		0.6	3		
		Read Mode		220	297		
VM7162 Power Dissipation	PD	Write Mode, I _W = 35mA Normal		395	479	mW	
		Servo		570	693		
		Sleep Mode		3	17		
		Read Mode		220	297		
VM7164, VM7168 Power Dissipation	PD	Write Mode, IW = 35mA Normal		445	545	mW	
		Servo		1050	1221		
		Sleep Mode		3	17		
Input High Voltage	VIH		2		V _{CC} + 0.3	٧	
Input Low Voltage	VIL		-0.3		0.8	٧	
Input High Current	ηн	V _{IH} = 2.7V			80	μА	
Input Low Current	կլ_	V _{IL} = 0.4V	-160			μА	
WUS Output Low Voltage	VOL	I _{OL} = 4.0mA		0.35	0.5	V	
WUS Output High Current	ЮН	V _{OH} = 5.0V		13	100	μА	
VCC Value for Write Current Turn Off		I _H < 0.2mA	3.7	4.0	4.3	٧	

Note 1: Typical values are given at $V_{CC} = 5V$ and $T_A = 25$ °C.

READ CHARACTERISTICS Recommended operating conditions apply unless otherwise specified; C_L (RDX, RDY) < 20pF, R_L (RDX, RDY) = 1k Ω .

PARAMETER	SYM	CONDITIONS		MIN	TYP (Note 1)	MAX	UNITS
			VM7162	250	300	350	V/V
Differential Voltage Gain	ΑV	V _{IN} = 1mVrms, 1MHz	VM7164	250	300	350	
			VM7168	210	250	290	
		-1dB Zs < 5Ω, V _{IN} = 1mVp-p)	30	40		MHz
Bandwidth	BW	-3dB Zs < 5Ω, V _{IN} = 1mVp-p)	55	75		IVITIZ
Input Noise Voltage	ein	BW = 17MHz, L _H = 0, R _H = 0			0.5	0.65	nV/√Hz
Differential Input Capacitance	CIN	V _{IN} = 1mVp-p, f = 5MHz			12	TBD	рF
Differential Input Resistance	RiN	V _{IN} = 1mVp-p, f = 5MHz		380	1000		Ω
Dynamic Range	DR	AC input where A _V is 90% of gain at 0.2mVrms input		2	5		mVrms
Common Mode Rejection Ratio	CMRR	V _{IN} = 100mVp-p @5MHz		50			dB
Power Supply Rejection Ratio	PSRR	100mVp-p @5MHz on VCC		45			dB
Channel Separation	cs	Unselected channels driven with 20mVp-p @5MHz		45			dB
Output Offset Voltage	Vos					+400	mV
RDX,RDY Common Mode Output Voltage	Vосм	Read Mode			V _{CC} -2.7		V
Read to Write Common Mode Output Voltage Difference	ΔVOCM			-350		350	mV
Single-Ended Output Resistance	RSEO					35	Ω
Output Current	lo	AC Coupled Load, RDX to RD	Y	±1.5			mA

Note 1: Typical values are given at V_{CC} = 5V and T_A = 25°C.

VM7162 (Two Channels), VM7164, VM7168 (Four Channels) Write

PARAMETER	SYM	CONDITIONS	MIN	TYP	MAX	UNITS
Write Current Matching Between Channels	ΔlW	5mA < I _W < 35mA			10	%
Duty Cycle (25mA/head)					20	%

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SWITCHING CHARACTERISTICS Recommended operating conditions apply unless otherwise specified; l_W = 20mA, f_{DATA} = 5MHz, L_H = 1 μ H, R_H = 30 Ω , C_L (RDX, RDY) \leq 20pF (see Figure 1).

PARAMETER	SYM	CONDITIONS		MIN	TYP (Note 1)	MAX	UNITS
R/W Read to Write Delay	tRW	R/W to 90% IW		0.04	0.2	μs	
R/W Write to Read Delay	twR	R/W to 90% of 100r envelope		0.4	1	μs	
WSER to Read Delay	tSR	R/W to 90% of 100r envelope. (WSER a switching)		0.4	1	μs	
CS Unselect to Select Delay	tiR	CS to 90% IW or 90 read signal envelop			0.6	μs	
CS Select to Unselect Delay	tRI	CS to 10% of IW			0.6	μs	
HS0, 1, any Head Delay	tHS	HS0, 1 to 90% of 100mV, 10MHz read signal envelope			-	0.6	μs
WUS Safe to Unsafe Delay	^t D1		0.6		3.6	μs	
WUS Unsafe to Safe Delay	tD2					1.0	μs
Head Current Propagation Delay (TD3)	tD3	L _H = 0, R _H = 0, from 50% points				30	ns
Head Current Asymmetry	ASYM	50% duty cycle on WDI, 1ns rise/fall time; L _H = 0, R _H = 0				0.5	ns
Head Current Rise/Fall Time	t _r /t _f	10% to 90% points	L _H = 0, R _H = 0		4	6	
			$L_{H} = 1 \mu H$, $R_{H} = 30 Ω$		12	16	ns

Note 1: Typical values are given at $V_{CC} = 5V$ and $T_A = 25$ °C.

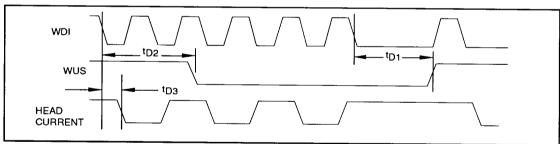


Figure 1: Write Mode Timing Diagram